





#### 100V NPN HIGH GAIN TRANSISTOR IN SOT223

#### **Features**

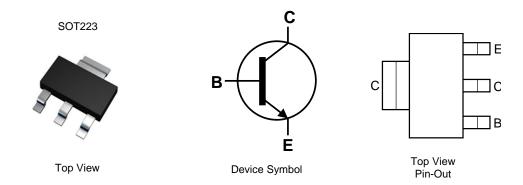
- BV<sub>CEX</sub> > 180V
- BV<sub>CEO</sub> > 100V
- BV<sub>ECO</sub> > 6V
- I<sub>C</sub> = 3A High Continuous Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 100mV @ 1A</li>
- $R_{CE(sat)} = 85m\Omega$
- Complementary PNP Type: ZXTP19100CG
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 <sup>®</sup>
- Weight: 0.112 grams (Approximate)

#### **Applications**

- PSU Start-Up Circuit
- DC-DC Converters
- Motor Drive
- · Relay, Lamp and Solenoid Drive



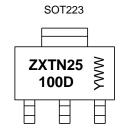
#### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25100DGTA	AEC-Q101	ZXTN25100D	7	12	1,000
ZXTN25100DGQTA	Automotive	ZXTN25100D	7	12	1,000

Notes:

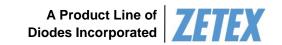
- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



ZXTN25100D = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)





#### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage (forward blocking)	V <sub>CEX</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Collector Voltage (reverse blocking)	V <sub>ECO</sub>	6	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	3	Α
Base Current	I <sub>B</sub>	1	Α
Peak Pulse Current	I <sub>CM</sub>	3.5	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		1.2 9.6		
Power Dissipation	(Note 7)		1.6 12.8	W mW/°C	
Linear Derating Factor	(Note 8)	P <sub>D</sub>	3 24		
	(Note 9)		5.3 42		
	(Note 6)		104		
Thermal Desistance, Junction to Ambient	(Note 7)		78		
Thermal Resistance, Junction to Ambient	(Note 8)	$R_{\theta JA}$	42	°C/W	
	(Note 9)		23.5		
Thermal Resistance, Junction to Lead (Note 10)		R <sub>0JL</sub>	16		
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C		

## ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С
Notes: 6. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air				

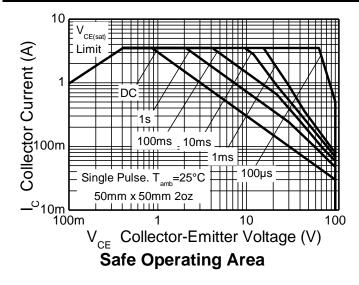
conditions whilst operating in steady-state.

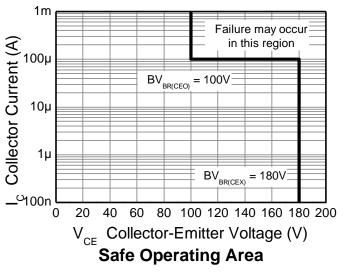
Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.

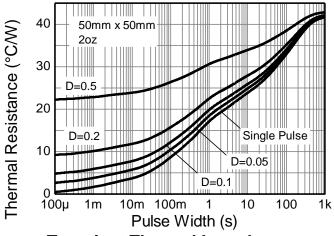
- Same as Note 6, except the device is mounted on 25mm x 25mm 102 copper.
   Same as Note 6, except the device is mounted on 50mm x 50mm 2oz copper.
   Same as Note 8 measured at t-5 seconds.
   Thermal resistance from junction to solder-point (at the end of the collector lead).
   Refer to JEDEC specification JESD22-A114 and JESD22-A115.

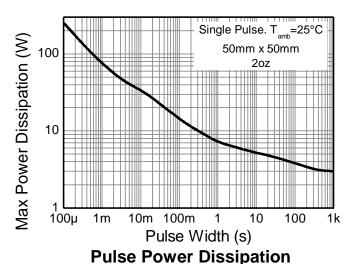


### Thermal Characteristics and Derating Information (@T<sub>A</sub> = +25°C, unless otherwise specified.)

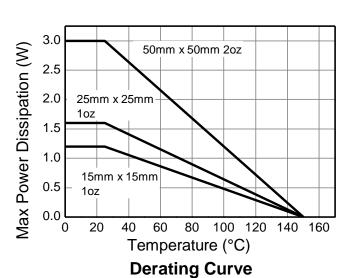








**Transient Thermal Impedance** 







# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

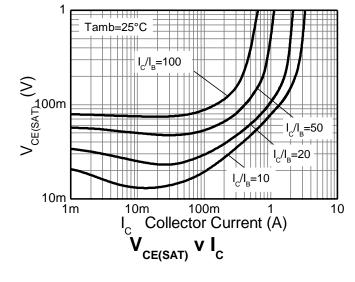
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	180	220	-	V	$I_{C} = 100 \mu A$	
Collector-Emitter Breakdown Voltage (forward blocking)	BV <sub>CEX</sub>	180	220	-	V	$I_C = 100\mu A$ , $R_{BE} < 1k\Omega$ or $-1V < V_{BC} > 0.25V$	
Collector-Emitter Breakdown Voltage (Note 12)	BV <sub>CEO</sub>	100	130	_	V	$I_C = 10mA$	
Emitter-Collector Breakdown Voltage (reverse blocking)	BV <sub>ECX</sub>	6	8.2	-	V	$I_C = 100\mu A, R_{BC} < 1k\Omega or$ 0.25V < $V_{BC} > -0.25V$	
Emitter-Collector Breakdown Voltage (reverse blocking)	BV <sub>ECO</sub>	6	8.7	_	V	I <sub>E</sub> = 100μA	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3	=	V	$I_E = 100\mu A$	
Collector Cut-Off Current	lone	_	< 1	50	nA	V <sub>CB</sub> = 180V	
Collector Cut-Oil Current	I <sub>CBO</sub>	-	-	0.5	μΑ	V <sub>CB</sub> = 180V, T <sub>A</sub> = 105°C	
Collector-Emitter Cut-Off Current	I <sub>CEX</sub>	_	-	100	nA	$V_{CE} = 100V, R_{BE} < 1k\Omega \text{ or}  -1V < V_{BC} > 0.25V$	
Emitter Cut-Off Current	I <sub>EBO</sub>	_	< 1	50	nA	V <sub>EB</sub> = 5.6V	
		_	120	170	mV	$I_C = 0.5A$ , $I_B = 10mA$	
Collector-Emitter Saturation Voltage (Note 12)	V <sub>CE(sat)</sub>	_	80	100	mV	$I_C = 1A$ , $I_B = 100mA$	
Collector-Emilier Saturation voltage (Note 12)		_	215	345	mV	$I_C = 2.5A$ , $I_B = 250mA$	
		-	200	500	mV	$I_C = 3A$ , $I_B = 600mA$	
Base-Emitter Saturation Voltage (Note 12)	$V_{BE(sat)}$	_	1020	1100	mV	$I_C = 3A$ , $I_B = 600mA$	
Base-Emitter Turn-On Voltage (Note 12)	$V_{BE(on)}$	_	905	1000	mV	$I_C = 3A$ , $V_{CE} = 2V$	
	h <sub>FE</sub>	300	450	900	-	$I_C = 10mA$ , $V_{CE} = 2V$	
DC Current Gain (Note 12)		120	170	=	=	$I_C = 0.5A$ , $V_{CE} = 2V$	
Do Guirent Gain (Note 12)		40	60	-	-	$I_C = 1A$ , $V_{CE} = 2V$	
		-	10	=	=	$I_C = 3A$ , $V_{CE} = 2V$	
Current Gain-Bandwidth Product (Note 12)	f⊤	_	175	-	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz	
Input Capacitance (Note 12)	C <sub>ibo</sub>	_	154	250	pF	$V_{EB} = 0.5V$ , $f = 1MHz$	
Output Capacitance (Note 12)	C <sub>obo</sub>	_	8.7	15	pF	V <sub>CB</sub> = 10V, f = 1MHz	
Delay Time	t <sub>d</sub>	_	16.4	_	ns		
Rise Time	t <sub>r</sub>	_	115		ns	$I_C = 500 \text{mA}, V_{CC} = 10 \text{V},$	
Storage Time	ts	_	763	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$	
Fall Time	t <sub>f</sub>	_	158	_	ns		

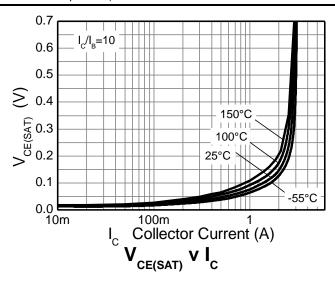
Note:

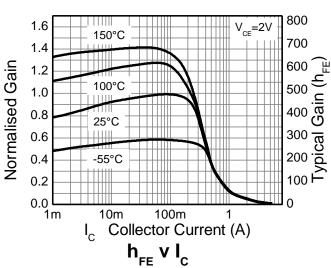
12. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

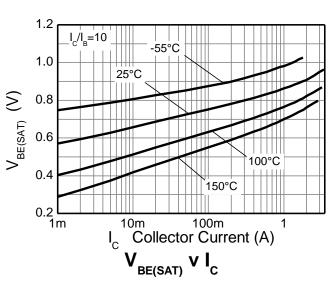


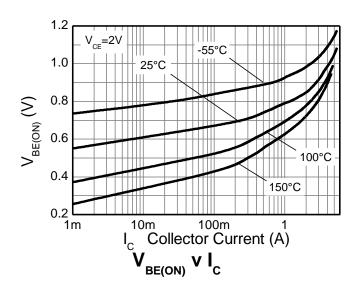
## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







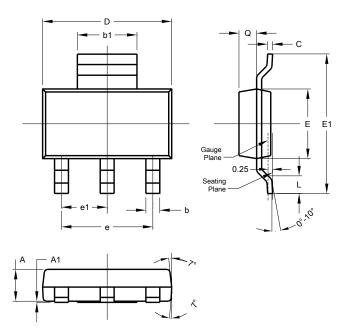






## **Package Outline Dimensions**

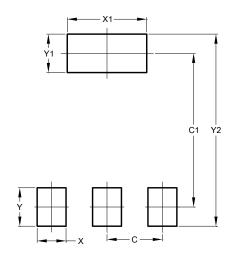
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

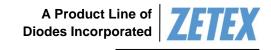
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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